

# NTE6410 Unijunction Transistor (UJT)

#### **Description:**

The NTE6410 is a PN unijunction transistor in a TO92 type package designed for use in pulse and timing circuits, sensing circuits and thyristor trigger circuits.

#### Absolute Maximum Ratings: (T<sub>A</sub> = +25°C unless other specified)

RMS Power Dissipation, P <sub>D</sub>	300mW 3.0mW/°C
RMS Emitter Current, I <sub>E</sub>	
Peak–Pulse Emitter Current (Note 1), I <sub>E</sub>	1.5A
Emitter Reverse Voltage, V <sub>B2E</sub>	30V
Interbase Voltage (Note 2), V <sub>B2B1</sub>	35V
Operating Junction Temperature Range, T <sub>J</sub>	–65° to +125°C
Storage Temperature Range, T <sub>stg</sub>	–65° to +150°C

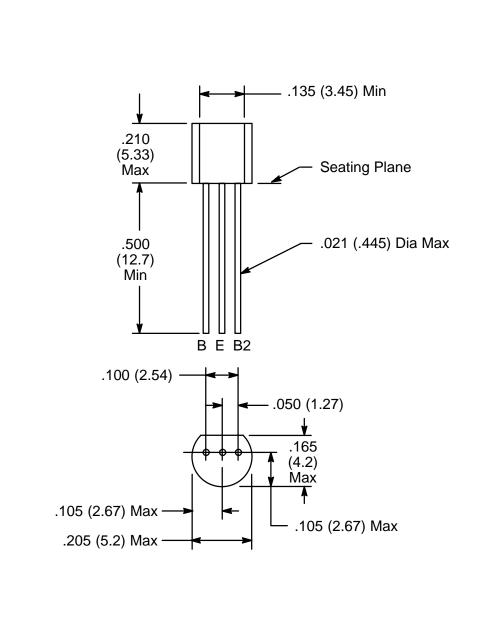
Note 1. Duty cycle  $\leq$  1%, PRR = 10 PPS

Note 2. Based upon power dissipation at  $T_A = +25^{\circ}C$ 

### **<u>Electrical Characteristics</u>**: (T<sub>A</sub> = +25°C unless other specified)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Intrinsic Standoff Ratio	η	V <sub>B2B1</sub> = 10V, Note 3	0.70	_	0.85	
Interbase Resistance	R <sub>BB</sub>		4.0	6.0	9.1	kΩ
Interbase Resistance Temperature Coefficient	$\alpha R_{BB}$		0.1	_	0.9	%/°C
Emitter Saturation Voltage	V <sub>BE1(sat)</sub>	$V_{B2B1} = 10V$ , $I_E = 50mA$ , Note 4	_	2.5	_	V
Modulated Interbase Current	I <sub>B2(Mod)</sub>	$V_{B2B1} = 10V, I_E = 50mA$	_	15	_	mA
Emitter Reverse Current	I <sub>EB2O</sub>	$V_{B2E} = 30V, I_{B1} = 0$	_	0.005	1.0	μΑ
Peak-Point Emitter Current	Ι <sub>Ρ</sub>	V <sub>B2B1</sub> = 25V	_	1.0	5.0	μΑ
Valley-Point Current	I <sub>V</sub>	$V_{B2B1} = 20V, R_{B2} = 100\Omega, Note 4$	4.0	7.0	_	mA
Base-One Peak Pulse Voltage	V <sub>OB1</sub>		5.0	8.0	_	V

- Note 3. Intrinsic standoff ratio, is defined in terms of peak–point voltage,  $V_P$ , by means of the equation:  $V_P = \eta \ V_{B2B1} \ V_F$ , where  $V_F$  is approximately 0.49 volts at +25°C @  $I_F = 10\mu A$  and decreases with temperature at approximately 2.5mV/°C. Components  $R_1$ ,  $C_1$ , and the UJT form a relaxation oscillator, the remaining circuitry serves as a peak–voltage detector. The forward drop of Diode  $D_1$  compensates for  $V_F$ . To use, the "call" button is pushed, and  $R_3$  is adjusted to make the current meter,  $M_1$ , read full scale. When the "call" button is released, the value of  $\eta$  is read directly from the meter, if full scale on the meter reads 1.0.
- Note 4. Use pulse techniques: PW  $\sim 300\mu s$ , duty cycle  $\leq 2.0\%$  to avoid internal heating, which may result in erroneous readings.



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